



**ZXTN2010G** 

### 60V NPN MEDIUM POWER LOW SATURATION TRANSISTOR **SOT223**

#### **Features**

- $BV_{CEO} > 60V$
- I<sub>C</sub> = 6A Continuous Collector Current
- I<sub>CM</sub> = 20A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(SAT)</sub> < 60mV Max @ 1A
- $R_{SAT}$  = 35m $\Omega$  @ I<sub>c</sub> =6A for Low Equivalent On-Resistance
- hFE Specified up to 10A for High Gain Hold Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

#### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.112 grams (Approximate)

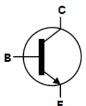
### Applications

- **Emergency Lighting Circuits**
- Motor Driving (Including DC Fans)
- Solenoid, Relay and Actuator Drivers
- DC Modules
- **Backlight Inverters**

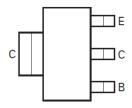
SOT223



Top View



**Device Schematic** 



Pin-Out Top View

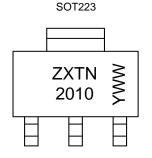
#### Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTN2010GTA	ZXTN2010	7	12	1,000

Notes: 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



ZXTN 2010 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 5= 2015) WW or  $\overline{W}W = \text{Week Code } (01~53)$ 

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# **Absolute Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	150	V
Collector-Emitter Voltage	V <sub>CEO</sub>	60	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	Ic	6	А
Peak Pulse Current	I <sub>CM</sub>	20	А

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)		3.0 24	W	
Linear Derating Factor	(Note 6)	P <sub>D</sub>	1.6 12.8	mW/°C	
Thermal Decistance Junction to Ambient	(Note 5)	$R_{\theta JA}$	42		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	78	°C/W	
Thermal Resistance, Junction to Lead (Note 7)		$R_{ heta JL}$	8.8		
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C		

### ESD Ratings (Note 8)

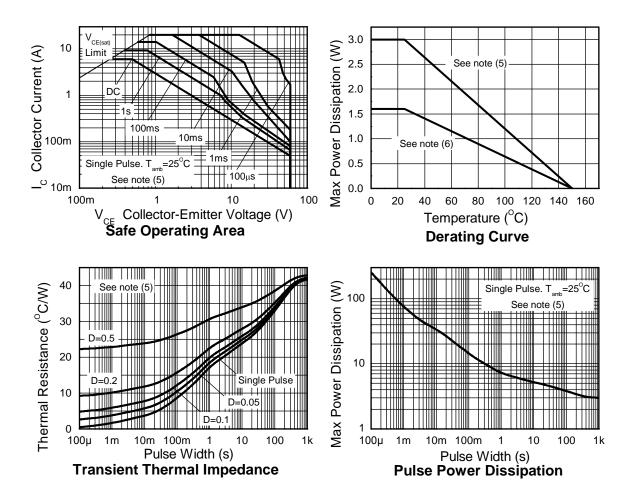
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
- Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
   Thermal resistance from junction to solder-point (at the end of the collector lead).
   Refer to JEDEC specification JESD22-A114 and JESD22-A115.



### **Thermal Characteristics and Derating Information**





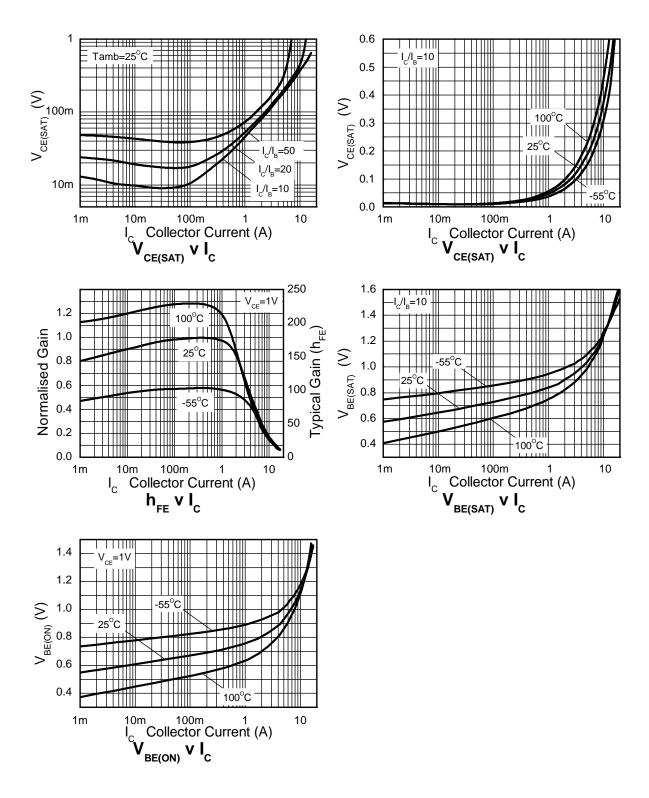
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		150	190	_	٧	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage		150	190	_	٧	$I_C = 1\mu A$ , RB $\leq 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)		60	80	_	V	$I_C = 10mA$
Emitter-Base Breakdown Voltage		7	8.1	_	٧	$I_E = 100\mu A$
Collector Cut-Off Current	I <sub>CBO</sub>	_	_	50 0.5	nΑ μΑ	V <sub>CB</sub> = 120V V <sub>CB</sub> = 120V, T <sub>A</sub> = +100°C
Collector Cut-Off Current	l <sub>CER</sub> R≤1kΩ	_	11	100 0.5	nΑ μΑ	V <sub>CB</sub> = 120V V <sub>CB</sub> = 120V, T <sub>A</sub> = +100°C
Emitter Cut-Off Current	I <sub>EBO</sub>	_	1	10	nA	$V_{EB} = 6V$
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(sat)</sub>	_ _ _ _	20 45 50 100 210	30 60 70 135 260	mV	$I_C = 0.1A$ , $I_B = 5mA$ $I_C = 1A$ , $I_B = 100mA$ $I_C = 1A$ , $I_B = 50mA$ $I_C = 2A$ , $I_B = 50mA$ $I_C = 6A$ , $I_B = 300mA$
Base-Emitter Saturation Voltage (Note 9)		_	1	1.1	V	$I_C = 6A$ , $I_B = 300mA$
Base-Emitter Saturation Voltage (Note 9) Base-Emitter Turn-on Voltage (Note 9)		_	0.94	1.05	V	$I_C = 6A, V_{CE} = 1V$
DC Current Gain (Note 9)	h <sub>FE</sub>	100 100 55 20	200 200 105 40	300 — —		$\begin{split} & I_{C} = 10 \text{mA},  V_{CE} = 1 \text{V} \\ & I_{C} = 2 \text{A},  V_{CE} = 1 \text{V} \\ & I_{C} = 5 \text{A},  V_{CE} = 1 \text{V} \\ & I_{C} = 10 \text{A},  V_{CE} = 1 \text{V} \end{split}$
Transition Frequency		_	130	_	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 100mA, f = 50MHz
Output Capacitance (Note 9)			31	_	pF	V <sub>CB</sub> = 10V, f = 1MHz
Switching Times			42 760		ns	$V_{CC} = 10V, I_C = 1A,$ $I_{B1} = -I_{B2} = 100mA$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

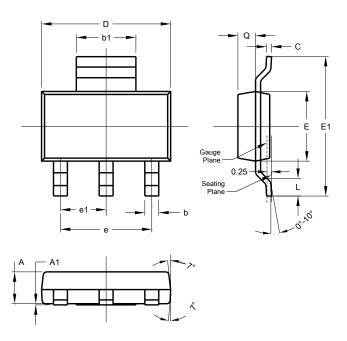




### **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### **SOT223**

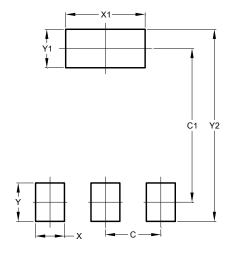


SOT223						
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All Dimensions in mm						

### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

### **SOT223**



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Y	1.60		
Y1	1.60		
Y2	8.00		



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